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(54) **BIASING OF RADIO-FREQUENCY SWITCHES**

(71) Applicant: **SKYWORKS SOLUTIONS, INC.**, Irvine, CA (US)

(72) Inventor: **Guillaume Alexandre BLIN**, Carlisle, MA (US)

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(57) **ABSTRACT**

In some embodiments, a switching circuit can include a first node and a second node, and a plurality of transistors implemented in a stack configuration between the first node and the second node, with each transistor having a source, a drain and a gate, and the transistors being configured to be in an ON state or an OFF state to respectively allow or inhibit passage of a signal between the first and second nodes. The switching circuit can further include a bias circuit configured to bias the transistors from a bias node. The bias circuit can include a gate-gate resistor that couples each pair of neighboring transistors of the plurality of transistors, and a feed node coupled to the bias node, with the feed node being connected directly to the gate of a selected transistor of the plurality of transistors.